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(54) **METHOD FOR COMPENSATING PROXIMITY EFFECTS OF PARTICLE BEAM LITHOGRAPHY PROCESSES**

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(52) **U.S. Cl.**
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See application file for complete search history.

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(57) **ABSTRACT**

A method for compensating proximity effects of particle beam lithography processes is provided. The method includes the following steps. A control pattern is provided. A dissection process is provided. A set of control points are provided. The control pattern is defined as an input pattern of a lithography process. A target pattern is provided. A set of target points are produced. A set of target measurement values are provided. An actual pattern is defined. A set of actual measurement values are provided. A set of comparison values are calculated. An adjusting strategy is provided. A corrected pattern is produced. The corrected pattern is defined as an updated input of the lithography process.

13 Claims, 3 Drawing Sheets